

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-to-Source Voltage		40	V	
V _{GS}	Gate-to-Source Voltage		±20	V	
I _D	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C =25°C 50		•	
	Pulsed Drain Current	T _C = 25°C	See Figure 4	Α	
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	39	mJ	
P _D	Power Dissipation		75	W	
	Derate Above 25°C		0.5	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C	
R _{0JC}	Thermal Resistance, Junction to Case		2	°C/W	
R _{0JA}	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	50	°C/W	

Notes:

1: Current is limited by bondwire configuration.

2: Starting $T_J = 25^{\circ}$ C, L = 0.1mH, $I_{AS} = 28A$, $V_{DD} = 40V$ during inductor charging and $V_{DD} = 0V$ during time in avalanche.

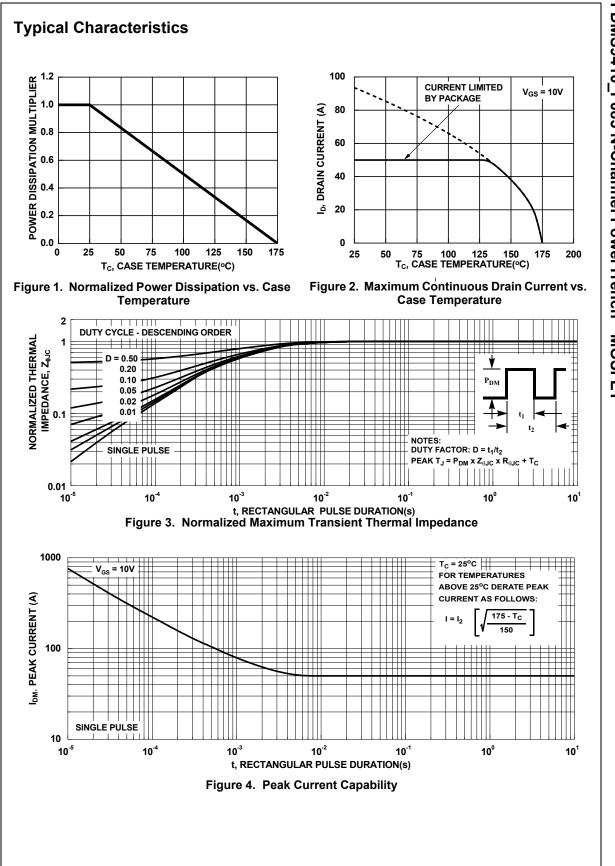
3: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design, while R_{0JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

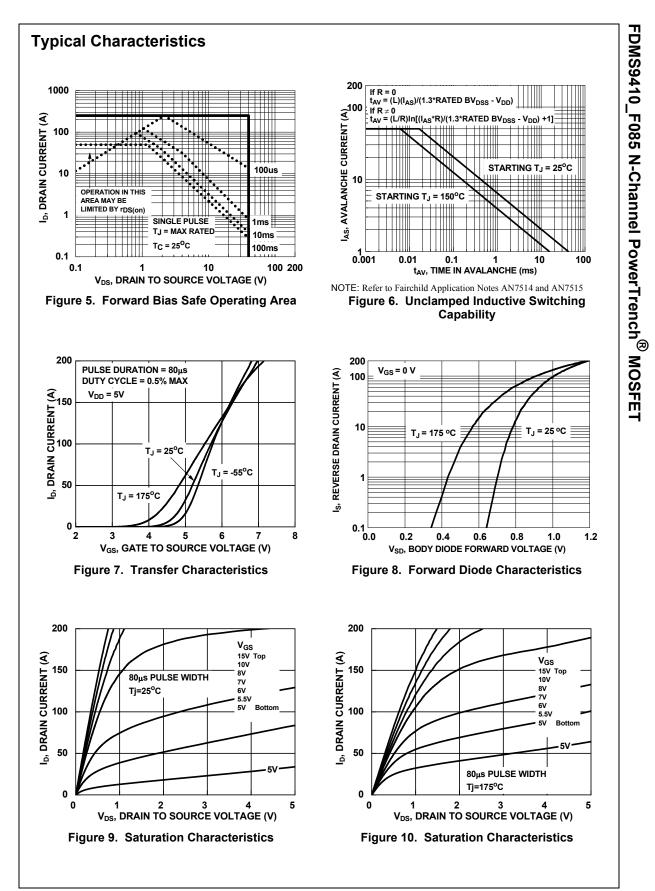
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS9410	FDMS9410_F085	Power56	13"	12mm	3000units

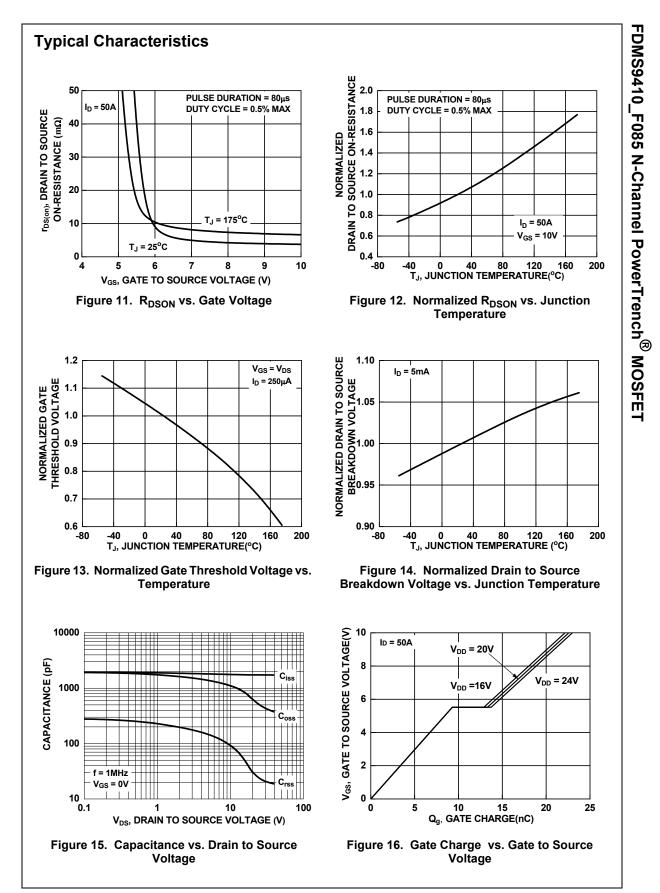
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
•	racteristics				.,,,,,		
B _{VDSS}	Drain-to-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V		40	-	-	V
		$V_{\rm DS}$ =40V, $T_{\rm J}$ = 25°C		-	-	1	μA
I _{DSS}	Drain-to-Source Leakage Current		$T_{\rm J} = 175^{\rm o}C$ (Note 4)	-	-	1	mA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} = ±20V		-	-	±100	nA
On Cha	racteristics						
V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I	_D = 250μA	2.0	3.2	4.0	V
		I _D = 50A,	T _J = 25°C	-	3.7	4.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	V_{GS} = 10V T_{J} = 175°C (Note 4)		6.6	7.9	mΩ
Dynami _{C_{iss}}	c Characteristics				1790	-	pF
C _{oss}	Output Capacitance	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz		-	620	-	pF
C _{rss}	Reverse Transfer Capacitance			-	32	-	pF
R _g	Gate Resistance	f = 1MHz	f = 1MHz		2.0	-	Ω
Q _{g(ToT)}	Total Gate Charge				24	36	nC
$Q_{q(th)}$	Threshold Gate Charge	• 00		-	3.3	-	nC
Q _{gs}	Gate-to-Source Gate Charge			-	9.1	-	nC
Q _{gd}	Gate-to-Drain "Miller" Charge			-	4.5	-	nC
Switchi	ng Characteristics				-	27	ns
t _{d(on)}	Turn-On Delay				12.1	-	ns
t _r	Rise Time	V _{DD} = 20V, I _D = 50A,		-	5.9	-	ns
t _{d(off)}	Turn-Off Delay	V _{GS} = 10V,	$V_{GS} = 10V, R_{GEN} = 6\Omega$		18.8	-	ns
t _f	Fall Time				5.0	-	ns
t _{off}	Turn-Off Time			-	-	31	ns
Drain-S	ource Diode Characteristics						
V _{SD}	Source-to-Drain Diode Voltage	I _{SD} =50A, V _{GS} = 0V		-	-	1.25	V
		I _{SD} = 25A, V		-	-	1.2	V
t _{rr}	Reverse-Recovery Time		_{SD} /dt = 100A/μs	-	45.5	59	ns
Q _{rr}	Reverse-Recovery Charge	$V_{DD} = 32V$		-	33.2	43	nC

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.



FDMS9410_F085 N-Channel PowerTrench[®] MOSFET





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